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# **EFC6612R**



http://onsemi.com

# Power MOSFET 20V, 5.1mΩ, 23A, Dual N-Channel

#### **Features**

- 2.5V drive
- Protection diode in
- Halogen free compliance

#### • Common-drain type

• 2KV ESD HBM

## **Applications**

• Lithium-ion battery charging and discharging switch

## **Specifications**

**Absolute Maximum Ratings** at Ta = 25°C

Parameter	Symbol	Conditions	Value	Unit
Source to Source Voltage	V <sub>SSS</sub>		20	٧
Gate to Source Voltage	V <sub>GSS</sub>		±12	V
Source Current (DC)	IS		23	Α
Source Current (Pulse)	ISP	PW≤100μs, duty cycle≤1%	100	Α
Total Dissipation	PT	When mounted on ceramic substrate (5000mm <sup>2</sup> ×0.8mm)	2.5	W
Junction Temperature	Tj		150	°C
Storage Temperature	Tstg		–55 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

## **Thermal Resistance Ratings**

Parameter	Symbol	Value	Unit	
Junction to Ambient	Do	50	°C/W	
When mounted on ceramic substrate (5000mm <sup>2</sup> ×0.8mm)	$R_{\theta JA}$	50	-0/00	

#### **Electrical Characteristics** at Ta = 25°C

Parameter	Symbol	Conditions		Value			Unit
Farameter	Symbol	Condit	10115	min	typ	max	Ullit
Source to Source Breakdown Voltage	V(BR)SSS	I <sub>S</sub> =1mA, V <sub>GS</sub> =0V	Test Circuit 1	20			V
Zero-Gate Voltage Source Current	ISSS	V <sub>SS</sub> =20V, V <sub>GS</sub> =0V	Test Circuit 1			1	μА
Gate to Source Leakage Current	IGSS	V <sub>GS</sub> =±8V, V <sub>SS</sub> =0V	Test Circuit 2			±1	μА
Gate Threshold Voltage	V <sub>GS</sub> (th)	V <sub>SS</sub> =10V, I <sub>S</sub> =1mA	Test Circuit 3	0.5	•	1.3	V
Forward Transconductance	gFS	V <sub>SS</sub> =10V, I <sub>S</sub> =3A	Test Circuit 4		4.7		S

Continued on next page.

#### **ORDERING INFORMATION**

See detailed ordering and shipping information on page 2 of this data sheet.

## **EFC6612R**

Continued from preceding page.

Description	O: ::==l==1	Conditions		Value			11-4
Parameter	Symbol			min	typ	max	Unit
	R <sub>SS</sub> (on)1	I <sub>S</sub> =4.5A, V <sub>GS</sub> =4.5V	Test Circuit 5	3.3	4.2	5.1	mΩ
	R <sub>SS</sub> (on)2	I <sub>S</sub> =4.5A, V <sub>GS</sub> =4.0V	Test Circuit 5	3.4	4.3	5.2	mΩ
Static Source to Source On-State Resistance	R <sub>SS</sub> (on)3	I <sub>S</sub> =4.5A, V <sub>GS</sub> =3.8V	Test Circuit 5	3.5	4.4	5.3	mΩ
nesistance	R <sub>SS</sub> (on)4	I <sub>S</sub> =4.5A, V <sub>GS</sub> =3.1V	Test Circuit 5	3.9	4.9	6.4	mΩ
	R <sub>SS</sub> (on)5	I <sub>S</sub> =4.5A, V <sub>GS</sub> =2.5V	Test Circuit 5	4.4	5.6	7.9	mΩ
Turn-ON Delay Time	t <sub>d</sub> (on)				30		ns
Rise Time	t <sub>r</sub>	V <sub>SS</sub> =10V, V <sub>GS</sub> =4.5V, I <sub>S</sub> =4.5A Test Circuit 6			640		ns
Turn-OFF Delay Time	t <sub>d</sub> (off)				11.8		μS
Fall Time	tf				92		μS
Total Gate Charge	Qg	V <sub>SS</sub> =10V, V <sub>GS</sub> =4.5V, I <sub>S</sub>	=23A Test Circuit 7		27		nC
Forward Source to Source Voltage	V <sub>F(S-S)</sub>	I <sub>S</sub> =4.5A, V <sub>GS</sub> =0V	Test Circuit 8		0.76	1.2	٧

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

## **Ordering & Package Information**

Device	Device Package Shipping		note	
EFC6612R-TF	EFCP	5,000 pcs. / reel	Pb-Free and Halogen Free	

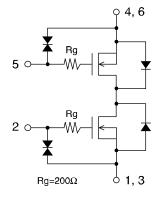
## **Packing Type: TF**



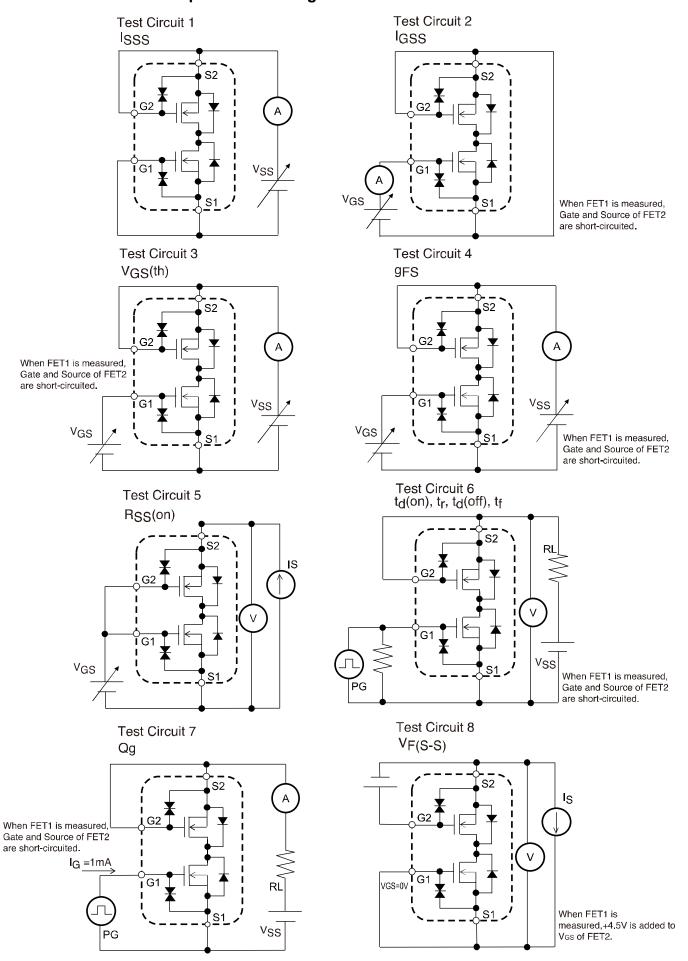
## Marking



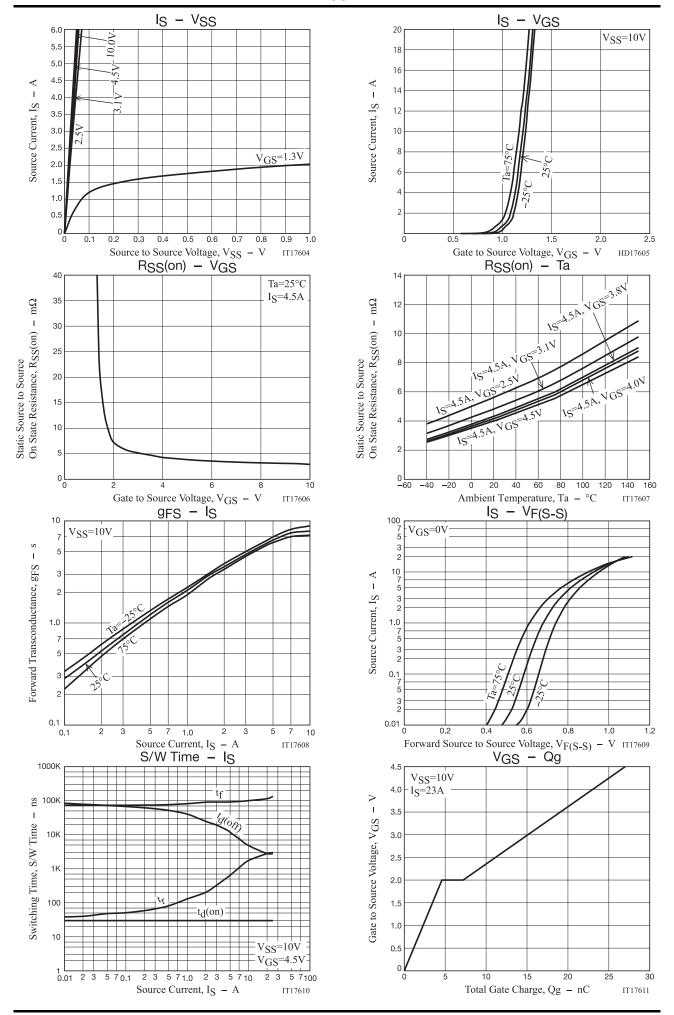
## **Electrical Connection**

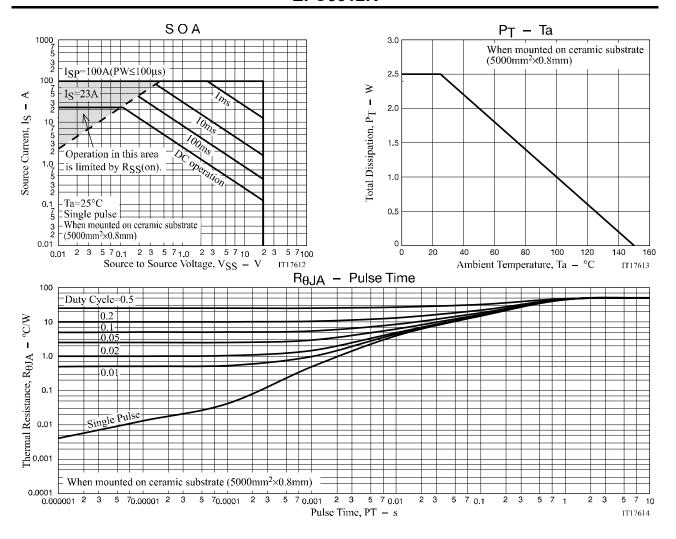


## Test circuits are example of measuring FET1 side



When FET2 is measured, the position of FET1 and FET2 is switched.





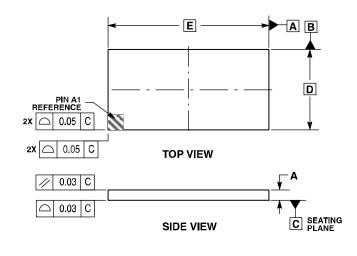
### **Package Dimensions**

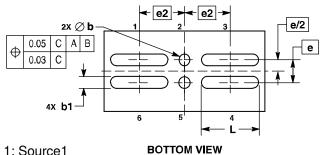
EFC6612R-TF

#### CSP6, 1.77×3.54 / EFCP3517-6DGH-020

CASE 568AL **ISSUE O** unit: mm







1: Source1

- 2: Gate1
- 3: Source1
- 4: Source2
- 5: Gate2
- 6: Source2

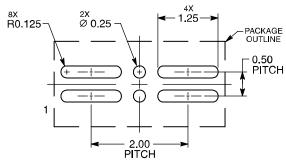
#### NOTES:

- ASTEES.

  1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
  2. CONTROLLING DIMENSION: MILLIMETERS.

	MILLIMETERS		
DIM	MIN MAX		
Α	_	0.22	
b	0,22	0.28	
<b>b</b> 1	0.22	0.28	
D	1.77 BSC		
E	3.54 BSC		
е	0.50 BSC		
e2	1.00 BSC		
L	1.22 1.28		

#### **RECOMMENDED** SOLDERING FOOTPRINT\*



**DIMENSIONS: MILLIMETERS** 

\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

Note on usage: Since the EFC6612R is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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